

Erratum to: 'Graphene Field-Effect Transistors With High Extrinsic f_T and f_{max} '

IEEE Electron Device Letters DOI [10.1109/LED.2018.2884054](https://doi.org/10.1109/LED.2018.2884054)

The original version of the article unfortunately contained an inaccuracy.

In Eq. (1), the denominator in the last term is missing. It should read as below with correction in red font:

$$f_T = \frac{g_m}{2 \pi (C_{gs} + C_{gd})} \frac{1}{1 + g_d R_c + \frac{C_{gd} g_m R_c}{C_{gs} + C_{gd}} + \frac{C_{pad}}{C_{gs} + C_{gd}}}$$

We confirm that it is just a misprint in the equation and all simulations in the paper are made using the correct relationship.